



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ\text{C}$
60V	$5\Omega @ V_{GS} = 10V$	250mA

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- DC-DC Converters
- Body Control Electronics

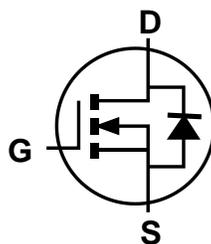
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

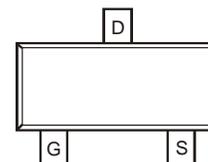
SOT23



Top View



Internal Schematic



Top View

Maximum Ratings (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_D	250	mA

Thermal Characteristics

Characteristic			Symbol	Value	Unit
Power Dissipation (Note 6)			P_D	300	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		$R_{\theta JA}$	417	$^\circ\text{C/W}$
Operating and Storage Temperature Range			T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 15\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	2.0	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	3.5	5.0	Ω	$V_{GS} = 10\text{V}, I_D = 0.2\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{ISS}	—	22	50	pF	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	C_{OSS}	—	11	25		
Reverse Transfer Capacitance	C_{RSS}	—	2.0	5.0		
Turn-On Delay Time	$t_{D(ON)}$	—	2.0	20	ns	$V_{ES} = 10\text{V}, R_L = 150\Omega,$ $V_{DS} = 10\text{V}, R_D = 100\Omega$
Turn-Off Delay Time	$t_{D(OFF)}$	—	5.0	20		

- Notes:
6. Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at <http://www.diodes.com/package-outlines.html>.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

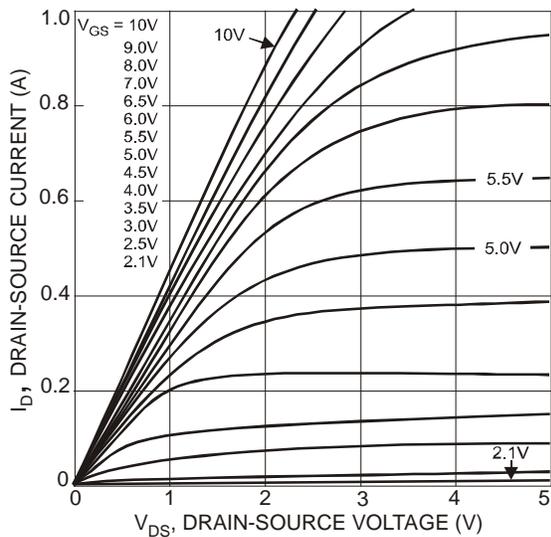


Fig. 1 On-Region Characteristics

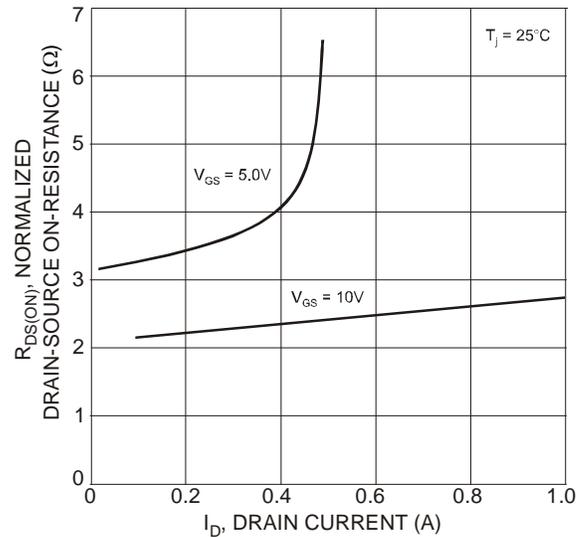


Fig. 2 On-Resistance vs. Drain Current

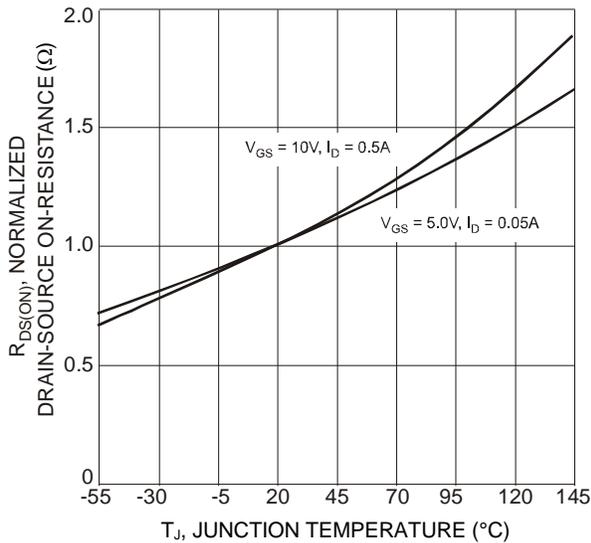


Fig. 3 On-Resistance vs. Junction Temperature

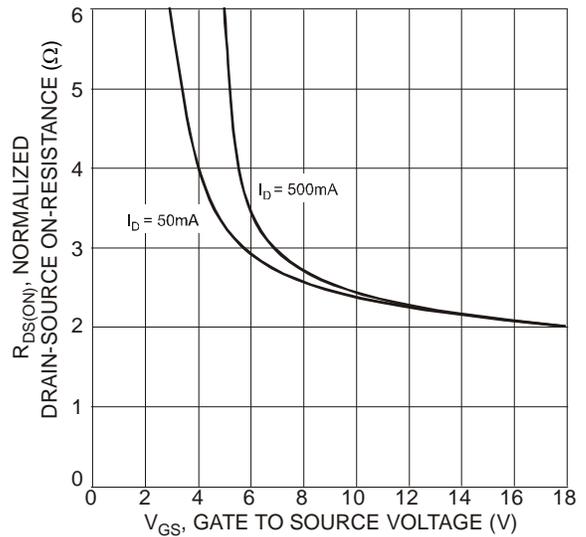


Fig. 4 On-Resistance vs. Gate-Source Voltage

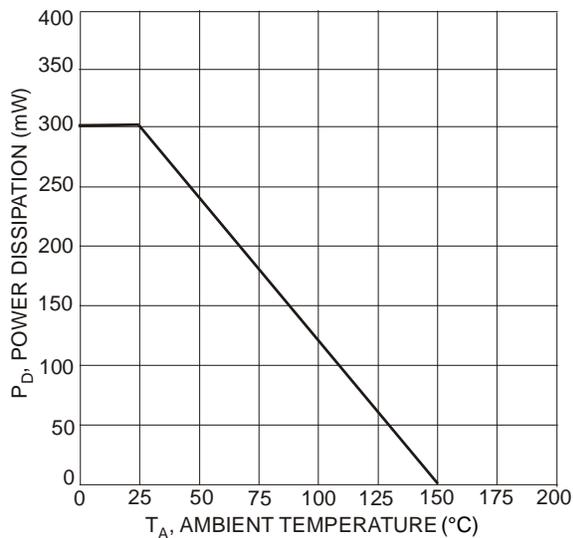
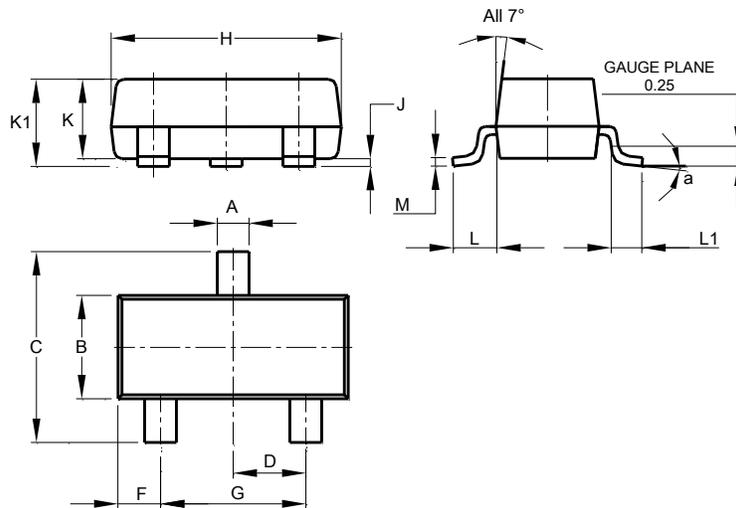


Fig. 5 Max Power Dissipation vs. Ambient Temperature

Package Outline Dimensions

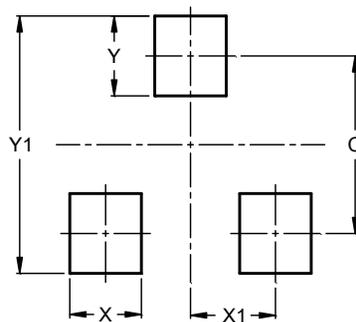
SOT23



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9